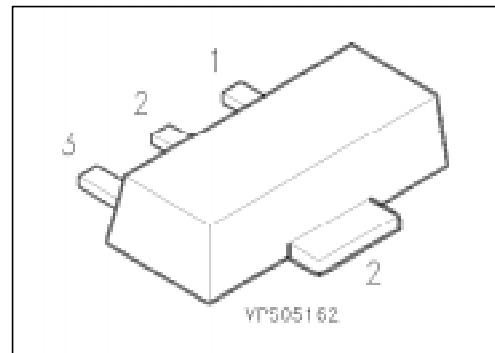


PNP Silicon Switching Transistor

SXT 3906

- High current gain: 0.1 mA to 100 mA
- Low collector-emitter saturation voltage



Type	Marking	Ordering Code (tape and reel)	Pin Configuration			Package ¹⁾
			1	2	3	
SXT 3906	2A	Q68000-A8397	B	C	E	SOT-89

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CE0}	40	V
Collector-base voltage	V_{CB0}	40	
Emitter-base voltage	V_{EB0}	5	
Collector current	I_C	200	mA
Total power dissipation, $T_S = 100^\circ\text{C}$	P_{tot}	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	- 65 ... + 150	

Thermal Resistance

Junction - ambient ²⁾	$R_{th JA}$	≤ 120	K/W
Junction - soldering point	$R_{th JS}$	≤ 50	

¹⁾ For detailed information see chapter Package Outlines.

²⁾ Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm² Cu.

Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC characteristics

Collector-emitter breakdown voltage $I_C = 1 \text{ mA}$	$V_{(\text{BR})\text{CE}0}$	40	—	—	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}$	$V_{(\text{BR})\text{CB}0}$	40	—	—	
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}$	$V_{(\text{BR})\text{EB}0}$	5	—	—	
Collector-base cutoff current $V_{\text{CB}} = 30 \text{ V}$	$I_{\text{CB}0}$	—	—	50	nA
Collector-emitter cutoff current $V_{\text{CE}} = 30 \text{ V}, V_{\text{BE}} = -3 \text{ V}$	I_{CEV}	—	—	50	
DC current gain $I_C = 100 \mu\text{A}, V_{\text{CE}} = 1 \text{ V}$ $I_C = 1 \text{ mA}, V_{\text{CE}} = 1 \text{ V}$ $I_C = 10 \text{ mA}, V_{\text{CE}} = 1 \text{ V}$ $I_C = 50 \text{ mA}, V_{\text{CE}} = 1 \text{ V}$ $I_C = 100 \text{ mA}, V_{\text{CE}} = 1 \text{ V}$	h_{FE}	60 80 100 60 30	— — — — —	— — 300 — —	—
Collector-emitter saturation voltage ¹⁾ $I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$	V_{CEsat}	— —	— —	0.25 0.4	V
Base-emitter saturation voltage ¹⁾ $I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$	V_{BESat}	0.65 —	— —	0.85 0.95	

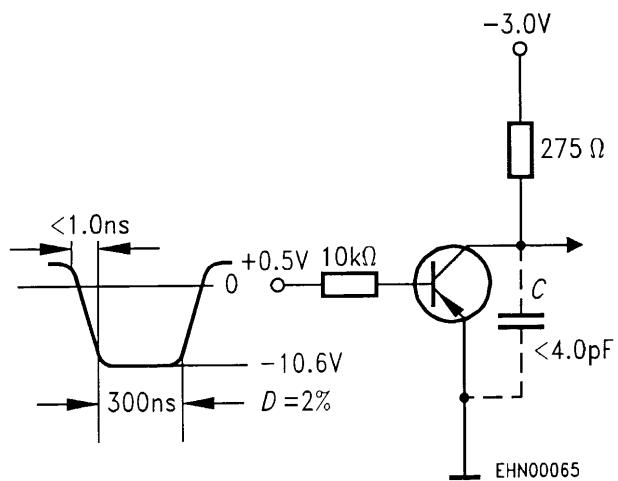
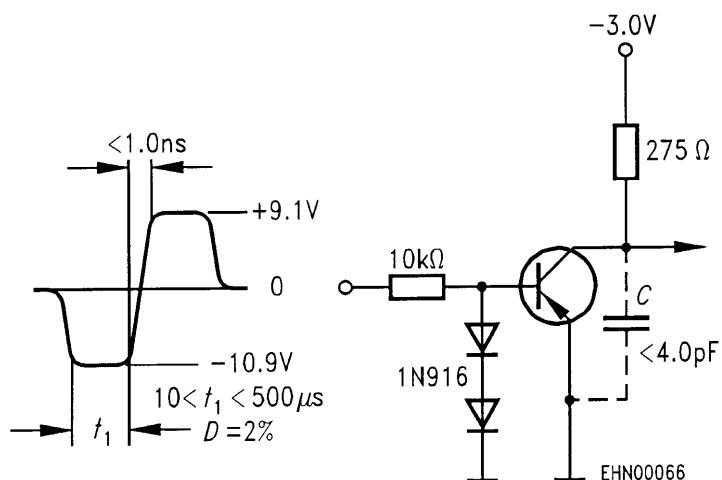
¹⁾ Pulse test conditions: $t \leq 300 \mu\text{s}$, $D \leq 2 \%$.

Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

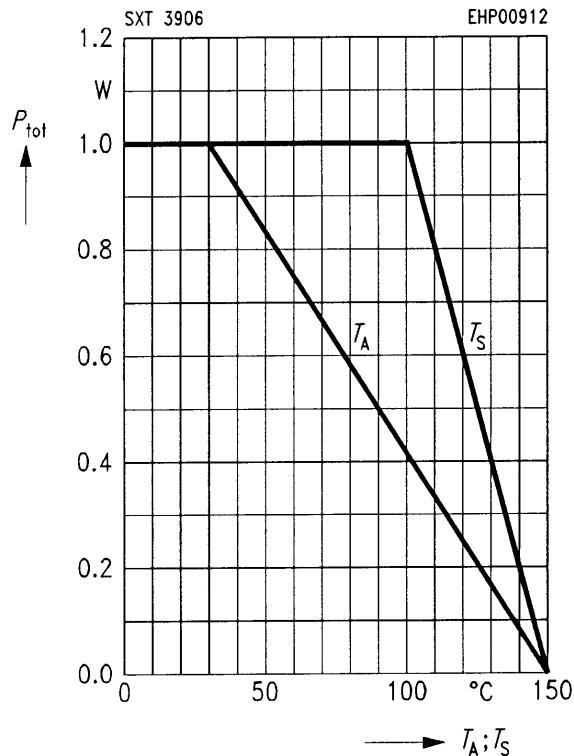
Parameter	Symbol	Values			Unit
		min.	typ.	max.	

AC characteristics

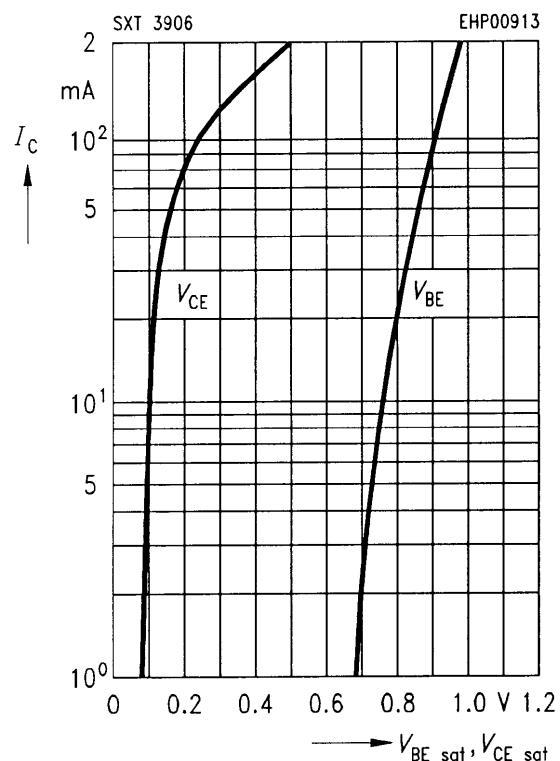
Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V}, f = 100 \text{ MHz}$	f_T	250	—	—	MHz
Output capacitance $V_{CB} = 5 \text{ V}, f = 1 \text{ MHz}$	C_{obo}	—	—	4.5	pF
Input capacitance $V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}$	C_{ibo}	—	—	10	
Input impedance $I_{CE} = 1 \text{ mA}, V_{CE} = 10 \text{ V}, f = 1 \text{ kHz}$	h_{ie}	2	—	12	kΩ
Voltage feedback ratio $I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}, f = 1 \text{ kHz}$	h_{re}	0.1	—	10	10^{-4}
Small-signal current gain $I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}, f = 1 \text{ kHz}$	h_{fe}	100	—	400	—
Output admittance $I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}, f = 1 \text{ kHz}$	h_{oe}	3	—	60	μS
Noise figure $I_C = 0.1 \text{ mA}, V_{CE} = 5 \text{ V}, f = 10 \text{ Hz to } 15 \text{ kHz}$ $R_S = 1 \text{ kΩ}$	NF	—	—	4	dB
Switching times $V_{CC} = 3 \text{ V}, V_{BE} = 0.5 \text{ V}, I_C = 10 \text{ mA},$ $I_{B1} = 1 \text{ mA}$	t_d t_r	— —	— —	35 35	ns ns
$V_{CC} = 3 \text{ V}, I_C = 10 \text{ mA},$ $I_{B1} = 1 \text{ mA}$	t_s t_f	— —	— —	225 75	ns ns

Test circuits**Delay and rise time****Storage and fall time**

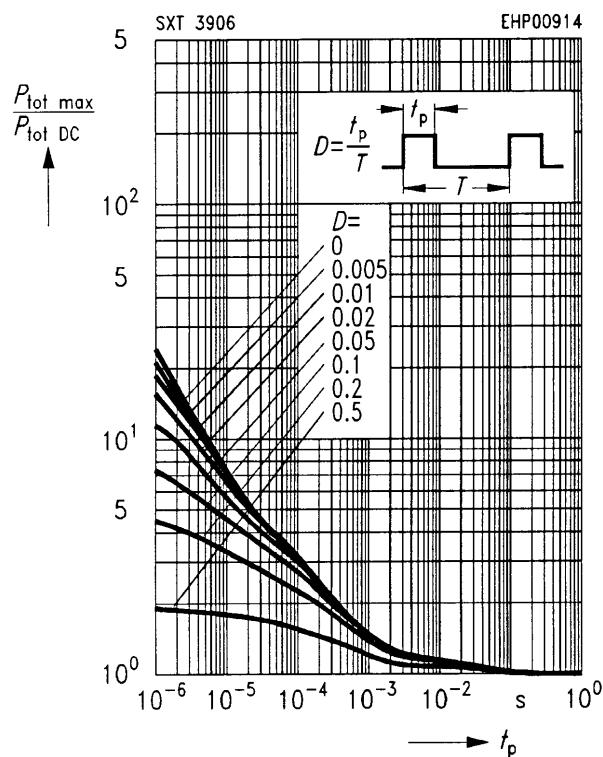
Total power dissipation $P_{\text{tot}} = f(T_A^*; T_S)$
 * Package mounted on epoxy



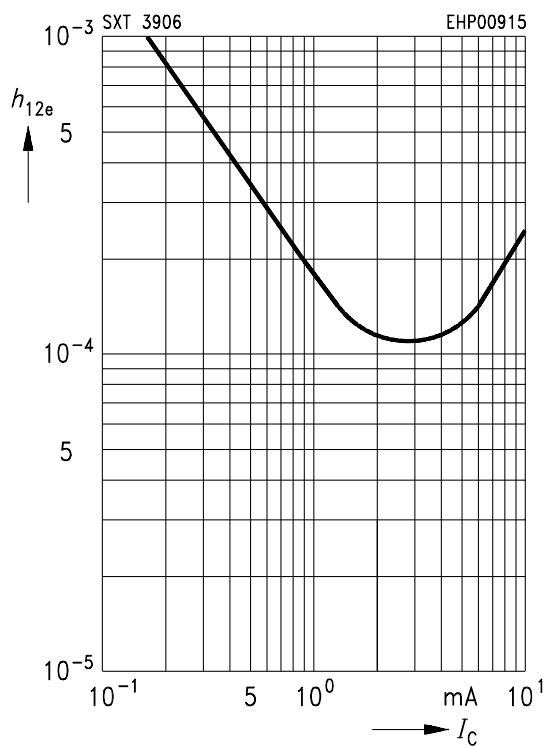
Saturation voltage $I_C = f(V_{BE \text{ sat}}, V_{CE \text{ sat}})$



Permissible pulse load $P_{\text{tot max}}/P_{\text{tot DC}} = f(t_p)$



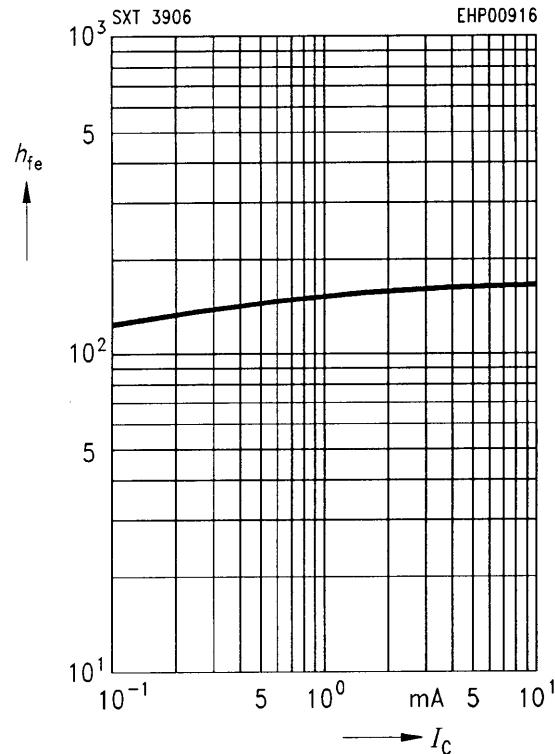
Open-circuit reverse voltage transfer ratio
 $h_{12e} = f(I_C)$



Small-signal current gain

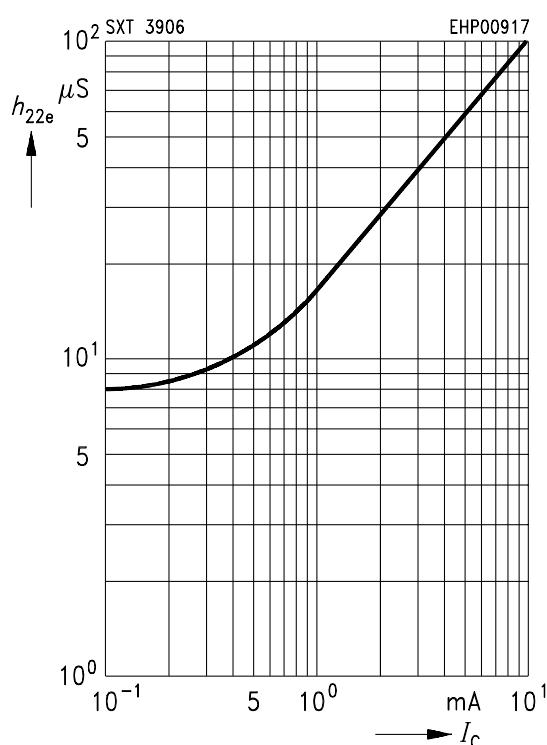
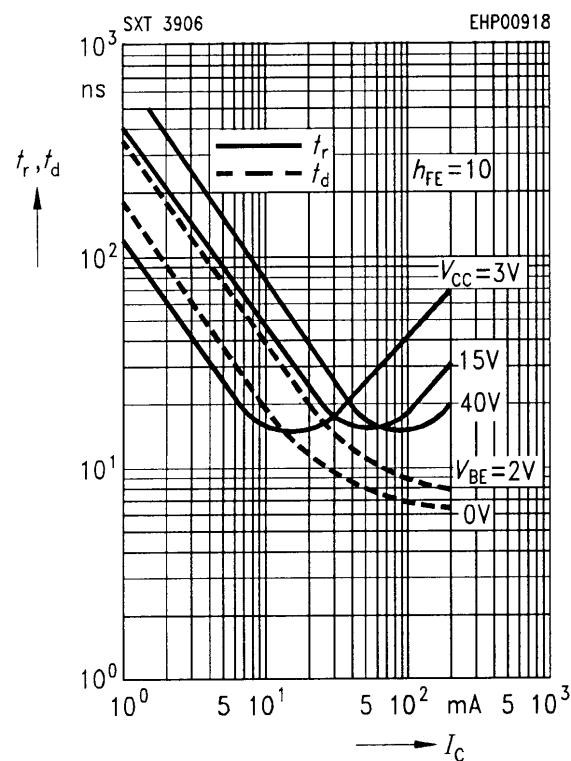
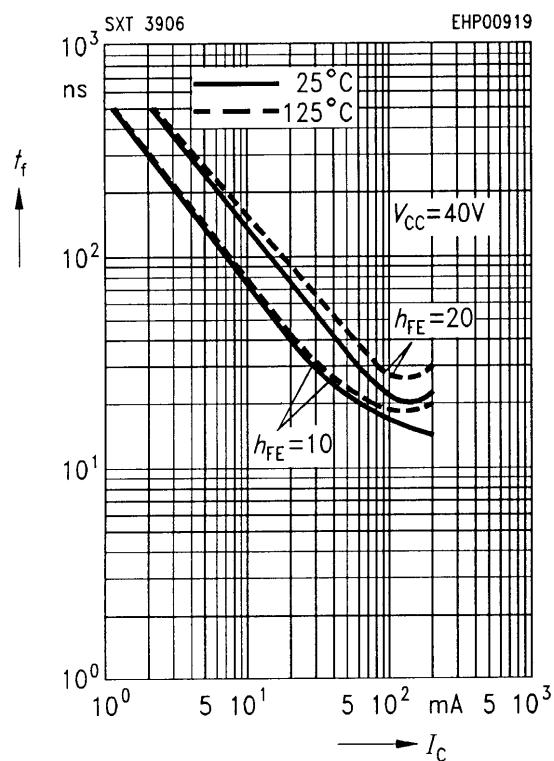
$$h_{fe} = f(I_c)$$

$V_{CE} = 10 \text{ V}$, $f = 1 \text{ MHz}$

**Output admittance**

$$h_{22e} = f(I_c)$$

$V_{CE} = 10 \text{ V}$, $f = 1 \text{ MHz}$

**Delay time $t_d = f(I_c)$** **Rise time $t_r = f(I_c)$** **Fall time $t_f = f(I_c)$** 

DC current gain $h_{FE} = f(I_C)$ $V_{CE} = 1 \text{ V}$, normalized